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FGAF40N60SMD 600 V, 40 A Field Stop IGBT

Features

- Maximum Junction Temperature : $T_J = 175^{\circ}C$
- · Positive Temperaure Co-efficient for easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: V_{CE(sat)} = 1.9 V(Typ.) @ I_C = 40 A
- High Input Impedance
- Fast Swiching: E_{OFF} = 6.5 uJ/A
- Tightened Parameter Distribution
- RoHS Compliant

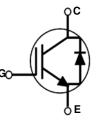
Applications

- · Sewing Machine, CNC
- · Home Appliances, Motor-Control

General Description

Using novel field stop IGBT technology, ON semiconductor's new series of field stop 2nd generation IGBTs offer the optimum performance for solar inverter, UPS, welder and PFC applications where low conduction and switching losses are essential.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit	
V _{CES}	Collector to Emitter Voltage		600	V	
V _{GES}	Gate to Emitter Voltage		± 20	V	
Ι _C	Collector Current	@ T _C = 25°C	80*	A	
	Collector Current	@ T _C = 100°C	40*	A	
I _{CM (1)}	Pulsed Collector Current		120*	A	
I _F	Diode Forward Current	@ T _C = 25°C	40*	A	
	Diode Forward Current	@ T _C = 100°C	20*	A	
I _{FM (1)}	Pulsed Diode Maximum Forward Cur	rrent	120*	A	
P _D	Maximum Power Dissipation	@ T _C = 25°C	115	W	
	Maximum Power Dissipation	@ T _C = 100°C	58	W	
TJ	Operating Junction Temperature		-55 to +175	°C	
T _{stg}	Storage Temperature Range		-55 to +175	°C	
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 secor	nds	300	°C	

Notes:

*Drain current limited by maximum junction temperature

1: Repetitive rating: Pulse width limited by max. junction temperature

Symbol Paramete			r Ty		р.	Max.	Unit			
R _{0JC} (IGBT) Thermal Resistance, Junction to Ca					<u> </u>	1.3		°C/W		
$R_{\theta,JC}(Diode)$ Thermal Resistance, Junction to Ca							3.27 ^o (°C/W	
$R_{\theta JA}$ Thermal Resistance, Junction to An						40	°C/W			
Packad	e Marki	ing and Orderi	na In	formatio	n					
Package Marking and Ordering In Device Marking Device Pa			ackage Reel Size		Tape Width		Quantity			
		FGAF40N60SMD		TO-3PF			•	-	30	
Electric	al Chai	racteristics of	the IC	GBT T 2	S ^o C uplace atho	nuiso notod				
Symbol		Parameter		Test Conditions			Min.	Тур.	Max.	Unit
Off Charge	toriotico									
BV _{CES}	Collector to Emitter Breakdown Voltage			V _{GE} = 0V, I _C	= 250µA		600	-	-	V
∆BV _{CES}		ure Coefficient of Break	0							
ΔT_J	Voltage			$V_{GE} = 0V, I_C = 250 \mu A$			-	0.6	-	V/°C
I _{CES}	Collector	Cut-Off Current		$V_{CE} = V_{CES}$	$V_{GE} = 0V$		-	-	250	μA
I _{GES}	G-E Leakage Current			$V_{GE} = V_{GES}, V_{CE} = 0V$		-	-	±400	nA	
On Charac	teristics									
V _{GE(th)}	1	G-E Threshold Voltage		$I_C = 250 \mu A$, $V_{CE} = V_{GE}$		3.5	4.5	6.0	V	
			I _C = 40A, V _{GE} = 15V		-	1.9	-	V		
V _{CE(sat)}	Collector to Emitter Saturation Voltage		$I_{C} = 40A, V_{GE} = 15V,$ $T_{C} = 175^{\circ}C$			-	2.1	-	V	
Dynamic C	haracteris	tics		•				1		
C _{ies}	Input Cap			$V_{CE} = 30V, V_{GE} = 0V,$			-	1880	-	pF
C _{oes}		apacitance					-	180	-	pF
C _{res}		Reverse Transfer Capacitance		f = 1MHz			-	50	-	pF
Switching	Characteri	stice								1
-		Delay Time					-	12	-	ns
t _r	Rise Time			-			-	20	-	ns
t _{d(off)}		Delay Time		V _{CC} = 400V,	lo = 4∩∆		-	92	-	ns
t _f	Fall Time	,		$R_{G} = 6\Omega, V_{G}$	_{ae} = 15V,		-	13	17	ns
E _{on}		Switching Loss		Inductive Lo	ad, T _C = 25	°C	-	0.87	-	mJ
E _{off}		Switching Loss		1			_	0.26	0.34	mJ
E _{ts}		ching Loss		1			-	1.13	-	mJ
t _{d(on)}		Delay Time					-	15	-	ns
t _r	Rise Time			V _{CC} = 400V, I _C = 40A,			-	22	-	ns
t _{d(off)}		Delay Time					-	116	-	ns
t _f	Fall Time	-		$R_{G} = 6\Omega, V_{C}$	_{BE} = 15V,		-	16	-	ns
E _{on}		Switching Loss		Inductive Load, T _C = 17		5°C	_	0.97	-	mJ
E _{off}		Switching Loss					-	0.60	-	mJ
011	1	0		1			L	1		

Electrical Characteristics of the IGBT (Continued)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
Qg	Total Gate Charge	V _{CE} = 400V, I _C = 40A, V _{GE} = 15V	-	119	-	nC
Q _{ge}	Gate to Emitter Charge		-	13	-	nC
Q _{gc}	Gate to Collector Charge		-	58	-	nC

Electrical Characteristics of the Diode $T_{C} = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max	Unit
V_{FM}	Diode Forward Voltage	I _F = 20A	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	2.3	-	v
			T _C = 175°C	-	1.67	-	
E _{rec}	Reverse Recovery Energy		T _C = 175°C	-	48.9	-	uJ
t _{rr}	Diode Reverse Recovery Time	I_F =20A, dI_F/dt = 200A/µs	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	36	-	ns
			T _C = 175°C	-	110	-	
Q _{rr}	Diode Reverse Recovery Charge		$T_{\rm C} = 25^{\rm o}{\rm C}$	-	46.8	-	nC
~11			T _C = 175°C	-	445	-	

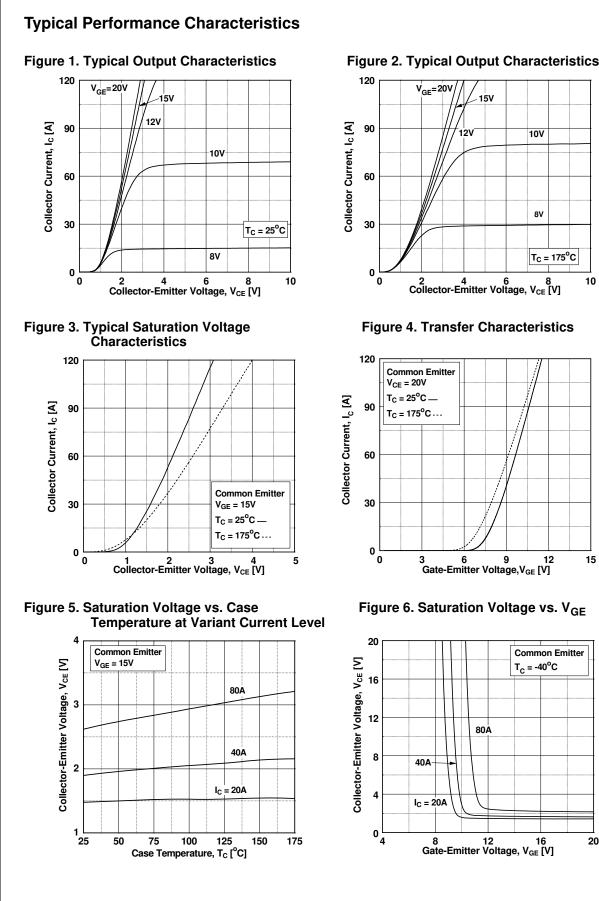


Figure 2. Typical Output Characteristics

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Typical Performance Characteristics



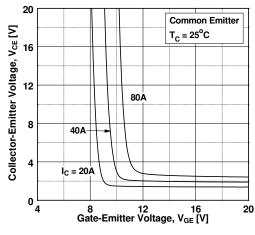


Figure 9. Capacitance Characteristics

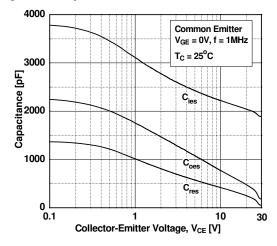


Figure 11. SOA Characteristics

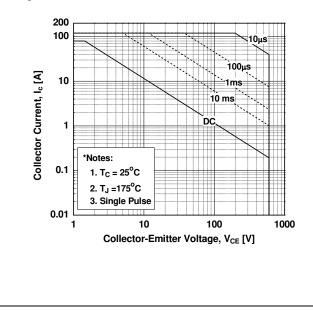


Figure 8. Saturation Voltage vs. V_{GE}

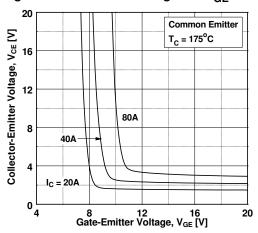


Figure 10. Gate charge Characteristics

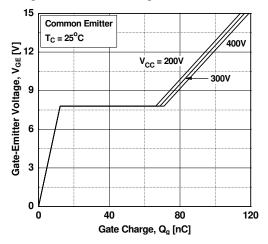
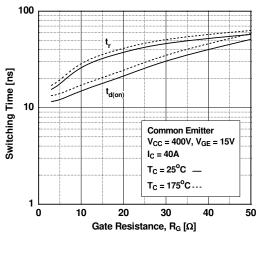
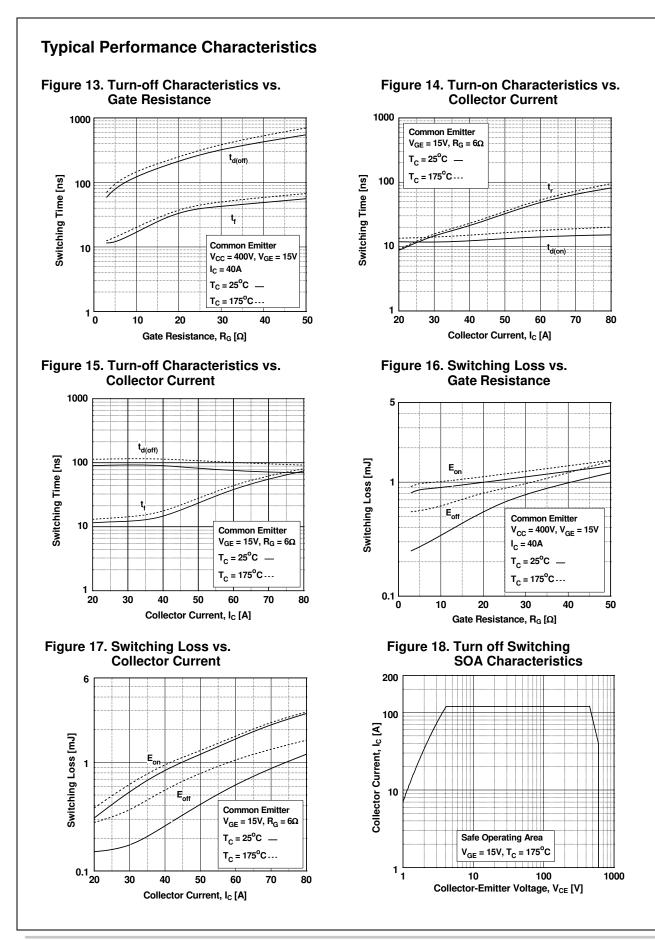
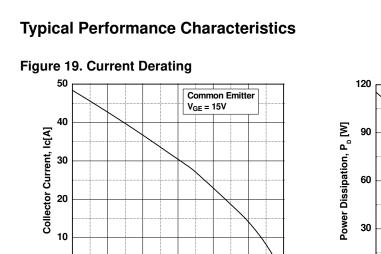


Figure 12. Turn-on Characteristics vs. Gate Resistance





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75

100

Case Temperature, T_C [°C]

125

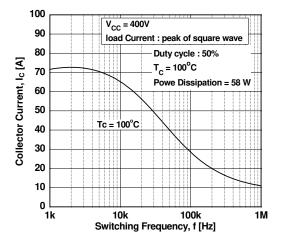
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175

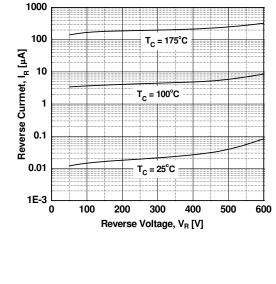
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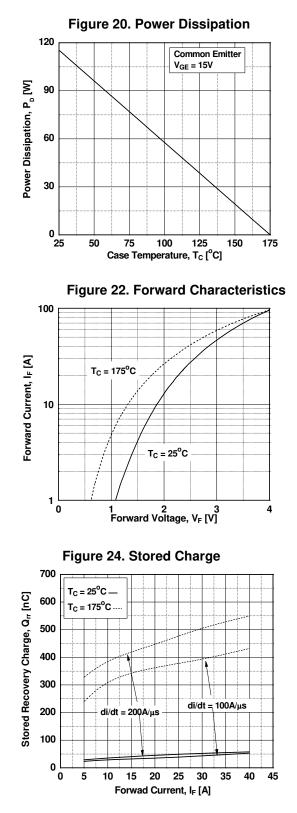
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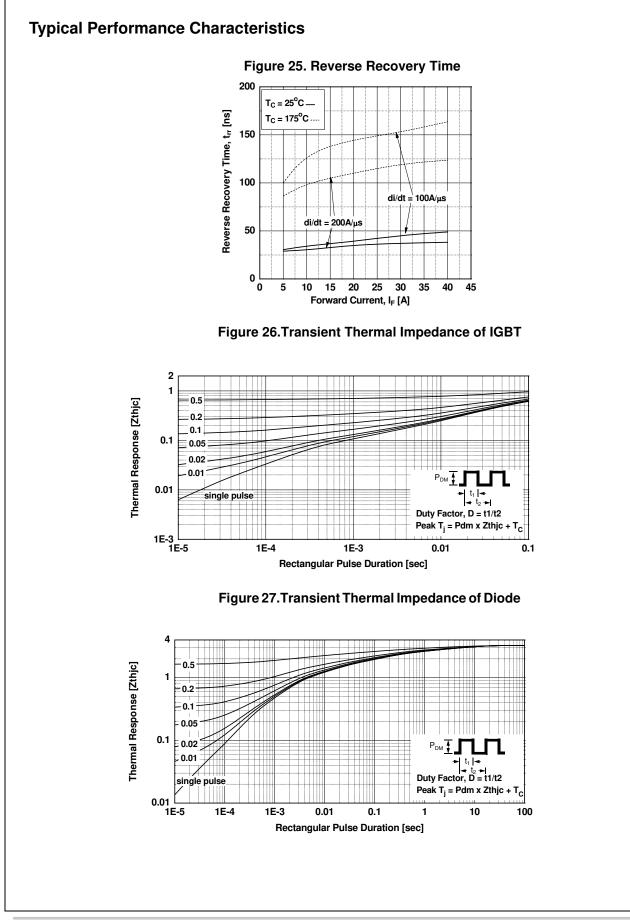
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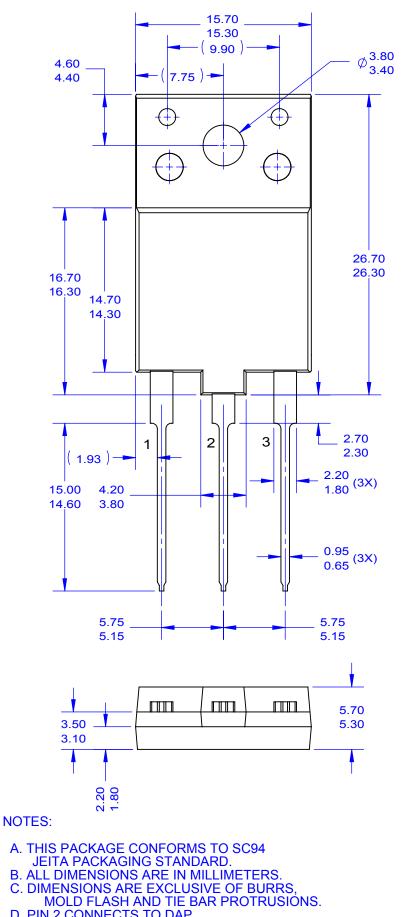




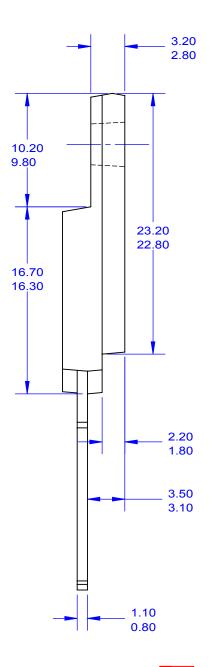














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